

BC816H series

80 V, 500 mA NPN general-purpose transistors

Rev. 1 — 26 March 2020

Product data sheet

1. General description

NPN general-purpose transistors in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package.

Table 1. Product overview

Type number	Package	NPN complement:	
	Nexperia	JEDEC	
BC816-16H	SOT23	TO-236AB	BC806-16H
BC816-25H	SOT23	TO-236AB	BC806-25H

2. Features and benefits

- · High current
- · High voltage
- · Two current gain selections
- High-temperature applications up to 175 °C
- AEC-Q101 qualified

3. Applications

- · General-purpose switching and amplification
- 48 V automotive board net

4. Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base; T _{amb} = 25 °C		-	-	80	V
I _C	collector current	T _{amb} = 25 °C		-	-	500	mA
I _{CM}	peak collector current	single pulse; $t_p \le 1$ ms; $T_{amb} = 25$ °C		-	-	1	Α
h _{FE}	DC current gain						
	BC816-16H	V _{CE} = 1 V; I _C = 100 mA T _{amb} = 25 °C	[1]	100	-	250	
	BC816-25H		[1]	160	-	400	

[1] pulsed; $t_p \le 300 \ \mu s$; $\delta \le 0.02$



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5. Pinning information

Table 3. Pinning

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	3	С
2	E	emitter		
3	С	collector		B — [
				Ė
			1 2	sym123
			TO-236AB (SOT23)	

6. Ordering information

Table 4. Ordering information

Type number	Type number Package				
	Name	Description	Version		
BC816-16H	TO-236AB	plastic, surface-mounted package; 3 leads	SOT23		
BC816-25H					

7. Marking

Table 5. Marking

100000000000000000000000000000000000000	
Type number	Marking code [1]
BC816-16H	QQ%
BC816-25H	QR%

[1] % = placeholder for manufacturing site code

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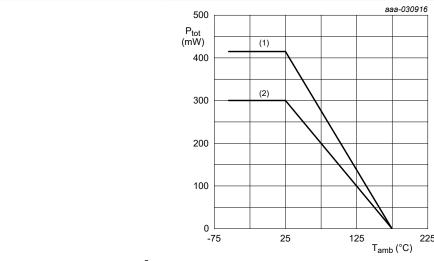
8. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter; T _{amb} = 25 °C	open emitter; T _{amb} = 25 °C		80	V
V _{CEO}	collector-emitter voltage	open base; T _{amb} = 25 °C		-	80	V
V _{EBO}	emitter-base voltage	open collector; T _{amb} = 25 °C		-	7	V
I _C	collector current	T _{amb} = 25 °C		-	500	mA
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms; T _{amb} =	25 °C	-	1	Α
I _{BM}	peak base current	single pulse; t _p ≤ 1 ms; T _{amb} =	25 °C	-	200	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	300	mW
			[2]	-	415	mW
Tj	junction temperature			-	175	°C
T _{amb}	ambient temperature			-55	175	°C
T _{stg}	storage temperature			-65	175	°C

- Device mounted on an FR4 Printed-Circuit-Board (PCB); single-sided copper; tin-plated and standard footprint. Device mounted on an FR4 PCB; single-sided copper; tin-plated; mounting pad for collector 1 cm².



- (1) FR4 PCB; 1 cm² mounting pad for collector
- (2) FR4 PCB; standard footprint

Power derating curves for SOT23 Fig. 1.

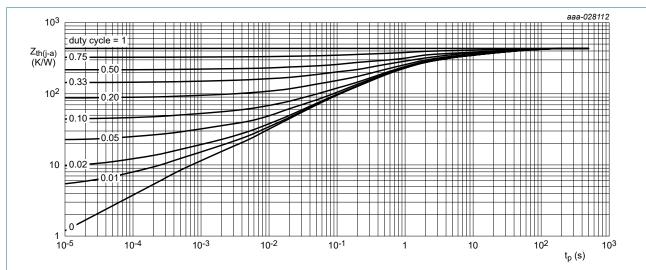
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9. Thermal characteristics

Table 7. Thermal characteristics

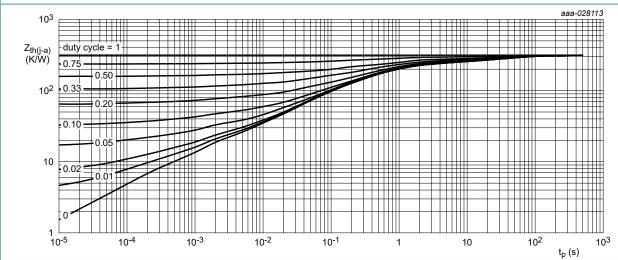
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	in free air;	[1]	-	-	500	K/W
		T _{amb} = 25 °C	[2]	-	-	363	K/W

- [1] Device mounted on an FR4 PCB; single-sided copper; tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB; single-sided copper; tin-plated; mounting pad for collector 1 cm².



FR4 PCB; single-sided copper; tin-plated and standard footprint

Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB; single-sided copper; tin-plated; mounting pad for collector 1 cm²

Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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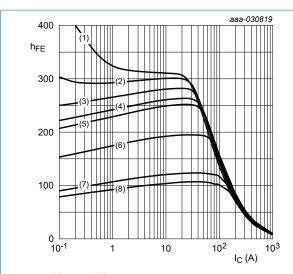
10. Characteristics

Table 8. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{(BR)CBO}$	collector-base breakdown voltage	I _C = 100 μA; I _E = 0 A; T _{amb} = 25 °C		80	-		V
V _{(BR)CEO}	collector-emitter breakdown voltage	$I_C = 2 \text{ mA}; I_E = 0 \text{ A}; T_{amb} = 25 \text{ °C}$		80	-		V
V _{(BR)EBO}	emitter-base breakdown voltage	I _E = 100 μA; I _C = 0 A; T _{amb} = 25 °C		7	-		V
I _{CBO}	collector-base	V _{CB} = 64 V; I _E = 0 A; T _{amb} = 25 °C		-	-	100	nA
	cut-off current	V _{CB} = 64 V; I _E = 0 A; T _j = 150 °C		-	-	5	μΑ
I _{EBO}	emitter-base cut-off current	V _{EB} = 5.6 V; I _C = 0 A; T _{amb} = 25 °C		-	-	100	nA
h _{FE} DC current gain				'		'	
	BC816-16H	V _{CE} = 1 V; I _C = 100 mA; T _{amb} = 25 °C	[1]	100	-	250	
	BC816-25H	V _{CE} = 1 V; I _C = 100 mA; T _{amb} = 25 °C	[1]	160	-	400	
		V _{CE} = 2 V; I _C = 500 mA; T _{amb} = 25 °C	[1]	30	-	-	
V _{CEsat}	collector-emitter	I _C = 100 mA; I _B = 10 mA; T _{amb} = 25 °C	[1]	-	-	150	mV
	saturation voltage	I _C = 500 mA; I _B = 50 mA; T _{amb} = 25 °C	[1]	-	-	400	mV
V _{BE}	base-emitter voltage	V _{CE} = 1 V; I _C = 500 mA; T _{amb} = 25 °C	[1]	-	-	1.2	V
f _T	transition frequency	V _{CE} = 5 V; I _C = 50 mA; f = 100 MHz; T _{amb} = 25 °C		100	-	-	MHz
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = i_e = 0 \text{ A}; f = 1 \text{ MHz}; $ $T_{amb} = 25 \text{ °C}$		-	2	-	pF
C _e	emitter capacitance	$V_{EB} = 0.5 \text{ V}; I_{C} = I_{c} = 0 \text{ A}; f = 1 \text{ MHz}; $ $T_{amb} = 25 \text{ °C}$		-	42	-	pF

^[1] pulsed; $t_p \le 300 \ \mu s$; $\delta \le 0.02$

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$$V_{CE} = 1 V$$

(1)
$$T_{amb} = 175 \, ^{\circ}C$$

(2)
$$T_{amb} = 150 \, ^{\circ}C$$

(3)
$$T_{amb} = 125 \, ^{\circ}C$$

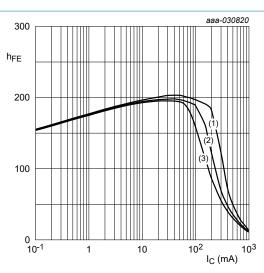
$$(5) T_{amb} = 85 °C$$

(6)
$$T_{amb}$$
 = 25 °C

(7)
$$T_{amb} = -40 \, ^{\circ}C$$

(8) $T_{amb} = -55 \, ^{\circ}C$

collector current; typical values



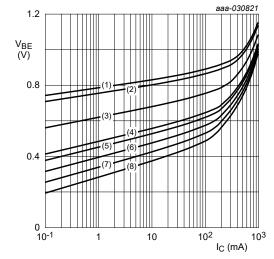
$$T_{amb}$$
 = 25 °C

(1)
$$V_{CE} = 5 V$$

(2)
$$V_{CE} = 2 V$$

(3)
$$V_{CE} = 1 V$$

Fig. 5. BC816-16H: DC current gain as a function of collector current; typical values



$$V_{CE} = 5 V$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb} = -40 \, ^{\circ}C$$

(3)
$$T_{amb}$$
 = 25 °C

(4)
$$T_{amb}$$
 = 85 °C

(5)
$$T_{amb} = 100 \, ^{\circ}C$$

$$(6) T_{amb} = 100 C$$

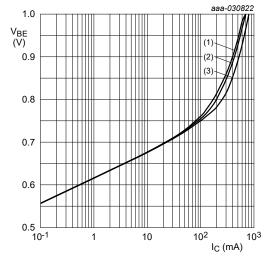
 $(6) T_{amb} = 125 °C$

(7)
$$T_{amb} = 150 \, ^{\circ}C$$

(8) $T_{amb} = 175 \, ^{\circ}C$

(c) ramb 170 C

Fig. 6. BC816-16H: Base-emitter voltage as a function of collector current; typical values



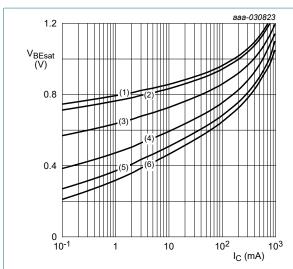
$$(1) V_{CE} = 1 V$$

(2)
$$V_{CE} = 2 V$$

(3)
$$V_{CE} = 5 V$$

Fig. 7. BC816-16H: Base-emitter voltage as a function of collector current; typical values

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IC/IB = 10

(1) $T_{amb} = -55 \, ^{\circ}C$

(2) $T_{amb} = -40 \, ^{\circ}C$

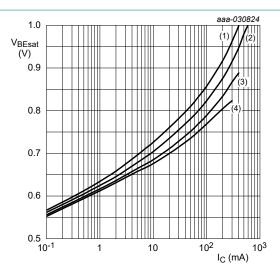
(3) T_{amb} = 25 °C

(4) $T_{amb} = 100 \, ^{\circ}C$

(5) $T_{amb} = 150 \, ^{\circ}C$

(6) $T_{amb} = 175 \, ^{\circ}C$

Fig. 8. BC816-16H: Base-emitter saturation voltage as a function of collector current; typical values



 $T_{amb} = 25 \, ^{\circ}C$

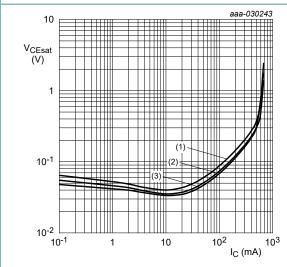
(1) IC/IB = 10

(2) IC/IB = 20

(3) IC/IB = 50

(4) IC/IB = 100

Fig. 9. BC816-16H: Base-emitter saturation voltage as a function of collector current; typical values



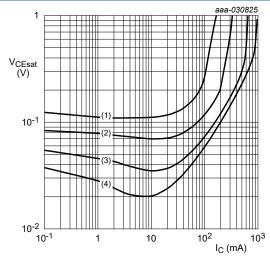
 $I_{\rm C}/I_{\rm B} = 20$

(1) $T_{amb} = 100 \, ^{\circ}C$

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = -40 \, ^{\circ}C$

Fig. 10. BC816-16H: Collector-emitter saturation voltage as a function of collector current; typical values | Fig. 11. BC816-16H: Collector-emitter saturation voltage



 $T_{amb} = 25 \, ^{\circ}C$

(1) IC/IB = 100

(2) IC/IB = 50

(3) IC/IB = 20

(4) IC/IB = 10

as a function of collector current; typical values

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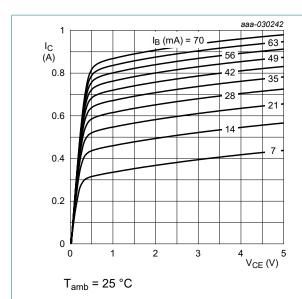
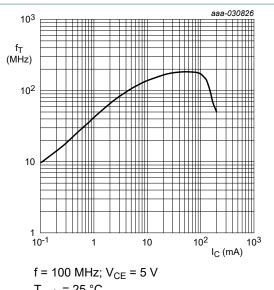


Fig. 12. BC816-16H: Collector current as a function of collector-emitter voltage; typical values



 T_{amb} = 25 °C

Fig. 13. BC816-16H: Transition frequency as a function of collector current; typical values

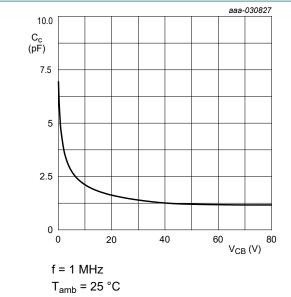
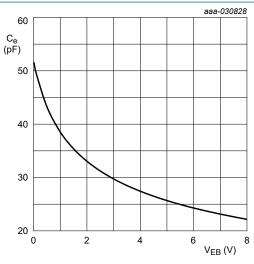


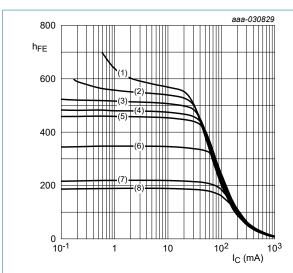
Fig. 14. BC816-16H: Collector capacitance as a function | Fig. 15. BC816-16H: Emitter capacitance as a function of collector-base voltage; typical values



f = 1 MHz $T_{amb} = 25 \, ^{\circ}C$

of emitter-base voltage; typical values

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 $V_{CE} = 1 V$

(1) $T_{amb} = 175 \, ^{\circ}C$

(2) $T_{amb} = 150 \, ^{\circ}C$

(3) $T_{amb} = 125 \, ^{\circ}C$

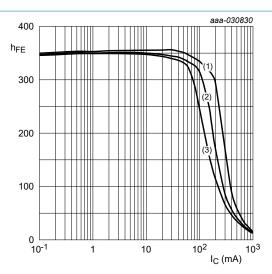
(4) $T_{amb} = 100 \, ^{\circ}C$

(5) T_{amb} = 85 °C

(6) T_{amb} = 25 °C

(7) $T_{amb} = -40 \, ^{\circ}C$ (8) $T_{amb} = -55 \, ^{\circ}C$

Fig. 16. BC816-25H: DC current gain as a function of collector current; typical values



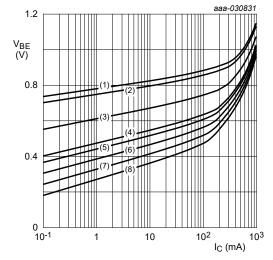
 $T_{amb} = 25 \, ^{\circ}C$

(1) $V_{CE} = 5 V$

(2) $V_{CE} = 2 V$

(3) $V_{CE} = 1 V$

Fig. 17. BC816-25H: DC current gain as a function of collector current; typical values



 $V_{CE} = 5 V$

(1) $T_{amb} = -55 \, ^{\circ}C$

(2) $T_{amb} = -40 \, ^{\circ}C$

(3) T_{amb} = 25 °C

(4) T_{amb} = 85 °C

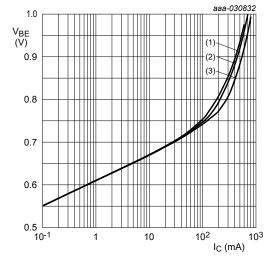
(5) $T_{amb} = 100 \, ^{\circ}C$

(6) T_{amb} = 125 °C

 $(7) T_{amb} = 150 °C$

(8) $T_{amb} = 175 \, ^{\circ}C$

Fig. 18. BC816-25H: Base-emitter voltage as a function of collector current; typical values



T_{amb} = 25 °C

 $(1) V_{CE} = 1 V$

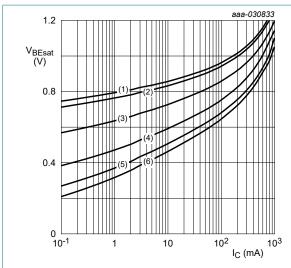
(2) $V_{CE} = 2 V$

(3) $V_{CE} = 5 V$

Fig. 19. BC816-25H: Base-emitter voltage as a function of collector current; typical values

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IC/IB = 10

(1) $T_{amb} = -55 \, ^{\circ}C$

(2) $T_{amb} = -40 \, ^{\circ}C$

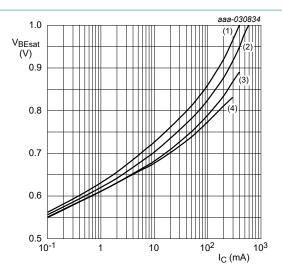
(3) T_{amb} = 25 °C

(4) $T_{amb} = 100 \, ^{\circ}C$

(5) $T_{amb} = 150 \, ^{\circ}C$

(6) $T_{amb} = 175 \, ^{\circ}C$

Fig. 20. BC816-25H: Base-emitter saturation voltage as a function of collector current; typical values



 $T_{amb} = 25 \, ^{\circ}C$

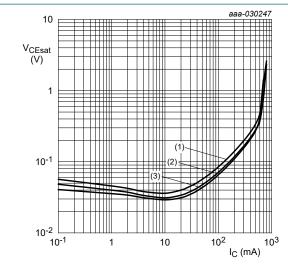
(1) IC/IB = 10

(2) IC/IB = 20

(3) IC/IB = 50

(4) IC/IB = 100

Fig. 21. BC816-25H: Base-emitter saturation voltage as a function of collector current; typical values



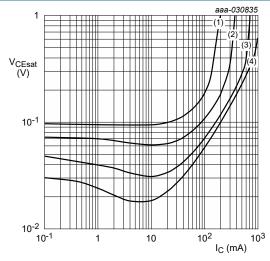
 $I_{\rm C}/I_{\rm B} = 20$

(1) $T_{amb} = 100 \, ^{\circ}C$

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = -40 \, ^{\circ}C$

Fig. 22. BC816-25H: Collector-emitter saturation voltage as a function of collector current; typical values | Fig. 23. BC816-25H: Collector-emitter saturation voltage



 $T_{amb} = 25 \, ^{\circ}C$

(1) IC/IB = 100

(2) IC/IB = 50

(3) IC/IB = 20

(4) IC/IB = 10

as a function of collector current; typical values

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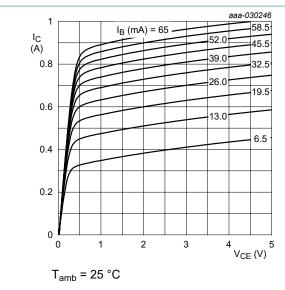
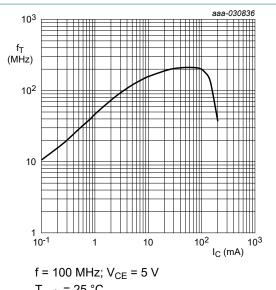
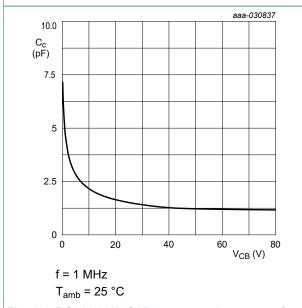


Fig. 24. BC816-25H: Collector current as a function of collector-emitter voltage; typical values

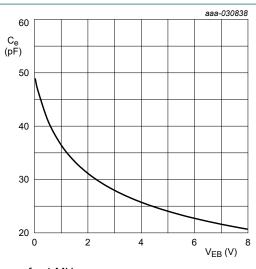


 $T_{amb} = 25 \, ^{\circ}C$

Fig. 25. BC816-25H: Transition frequency as a function of collector current; typical values



of collector-base voltage; typical values



f = 1 MHz $T_{amb} = 25 \, ^{\circ}C$

Fig. 26. BC816-25H: Collector capacitance as a function Fig. 27. BC816-25H: Emitter capacitance as a function of emitter-base voltage; typical values

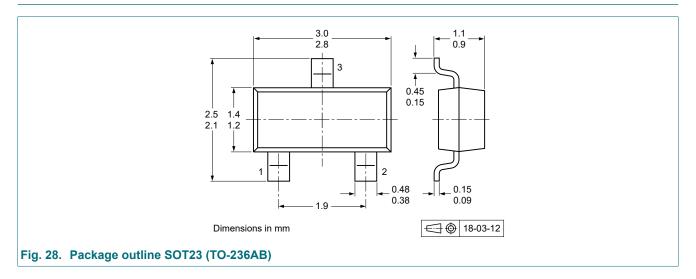
11. Test information

11.1. Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

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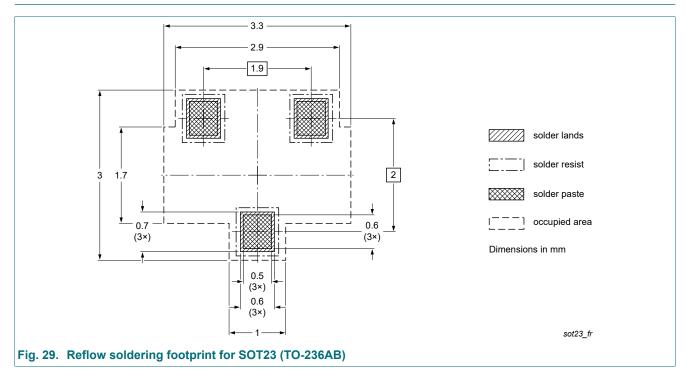
12. Package outline

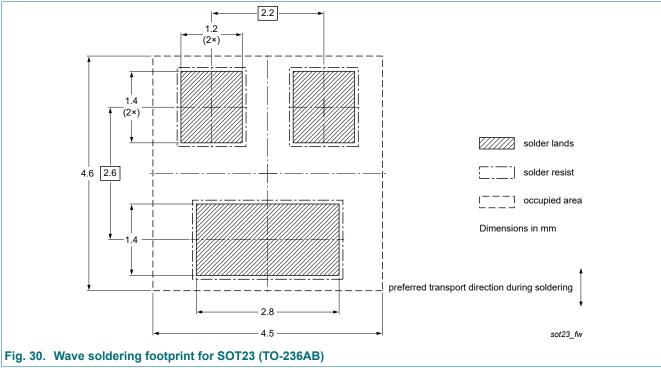


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13. Soldering





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14. Revision history

Table 9. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
BC816H_SER v.1	20200326	Product data sheet	-	-

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15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
- The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the internet at https://www.nexperia.com.

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80 V, 500 mA NPN general-purpose transistors

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